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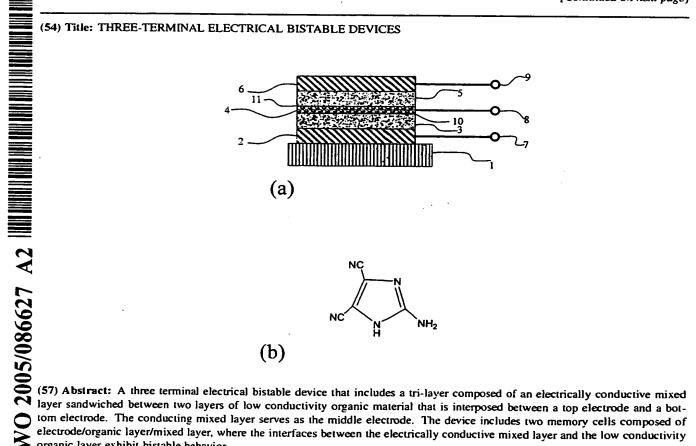
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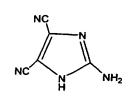
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(54) Title: THREE-TERMINAL ELECTRICAL BISTABLE DEVICES





tom electrode. The conducting mixed layer serves as the middle electrode. The device includes two memory cells composed of electrode/organic layer/mixed layer, where the interfaces between the electrically conductive mixed layer and the low conductivity organic layer exhibit bistable behavior.

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